

NEW PRODUCT

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max $T_c = +25^\circ C$
-60V	105m Ω @ $V_{GS} = -10V$	-7.3A
	130m Ω @ $V_{GS} = -4.5V$	-6.5A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

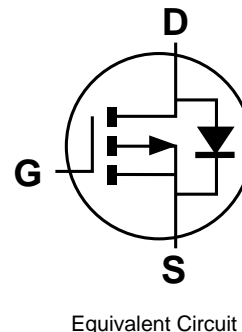
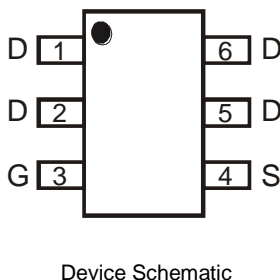
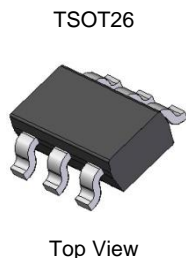
Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **e3**
- Weight: 0.008 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMP6110SVT-7	TSOT26	3,000/Tape & Reel
DMP6110SVT-13	TSOT26	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



P61 = Product Type Marking Code
 YM or YM = Date Code Marking
 Y or Y = Year (ex: C = 2015)
 M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021
Code	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	T _C = +25°C	-7.3
		T _C = +70°C	-5.8
Maximum Body Diode Forward Current (Note 6)	I _S	-1.8	A
Pulsed Drain Current (380µs Pulse, 1% Duty Cycle)	I _{DM}	-24	A
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-19	A
Repetitive Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	18	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	T _A = +25°C	1.2
		T _A = +70°C	0.75
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady state	105
		t < 10s	60
Total Power Dissipation (Note 6)	P _D	T _A = +25°C	1.8
		T _A = +70°C	1.1
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady state	69
		t < 10s	39
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	15	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1	—	-3	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	105	mΩ	V _{GS} = -10V, I _D = -4.5A
		—	—	130		V _{GS} = -4.5V, I _D = -3.5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	969	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	57	—		
Reverse Transfer Capacitance	C _{RSS}	—	44	—		
Gate Resistance	R _G	—	13.7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	8.2	—	nC	V _{DS} = -30V, I _D = -12A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	17.2	—		
Gate-Source Charge	Q _{gs}	—	3.0	—		
Gate-Drain Charge	Q _{gd}	—	3.1	—		
Turn-On Delay Time	t _{D(ON)}	—	4.4	—	ns	V _{GS} = -10V, V _{DS} = -30V, R _{GEN} = 3Ω, I _D = -12A
Turn-On Rise Time	t _R	—	23	—		
Turn-Off Delay Time	t _{D(OFF)}	—	34	—		
Turn-Off Fall Time	t _F	—	42	—		
Body Diode Reverse Recovery Time	t _{RR}	—	13.2	—	ns	I _S = -12A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	6.18	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

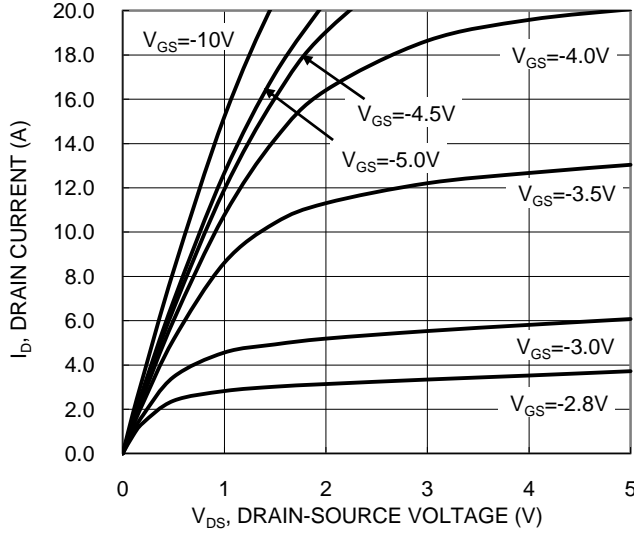


Figure 1. Typical Output Characteristic

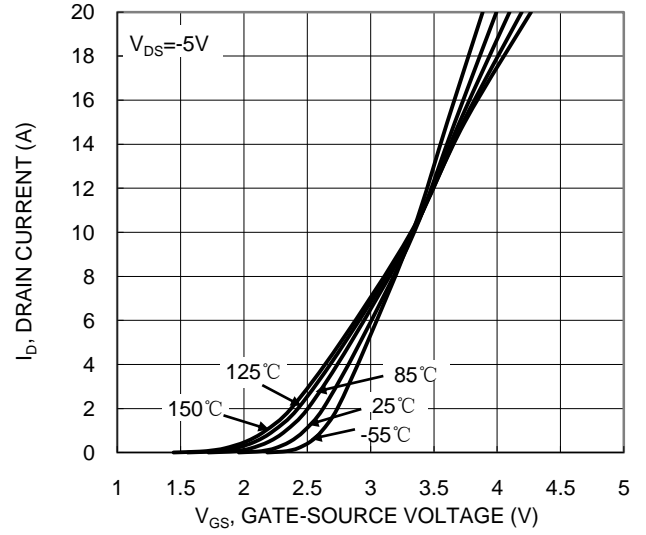


Figure 2. Typical Transfer Characteristic

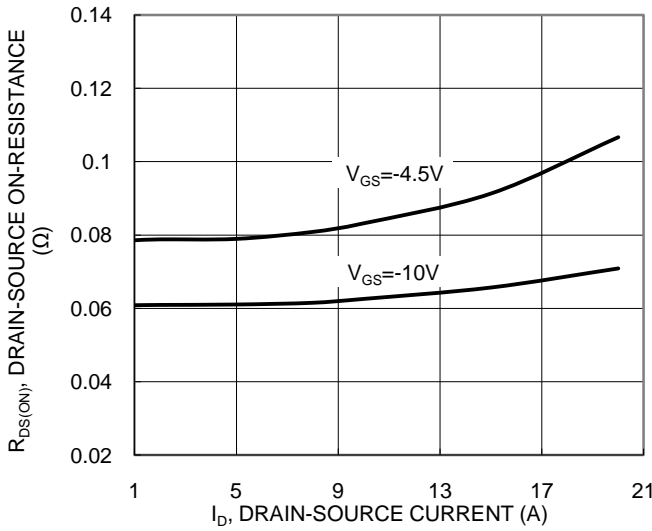


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

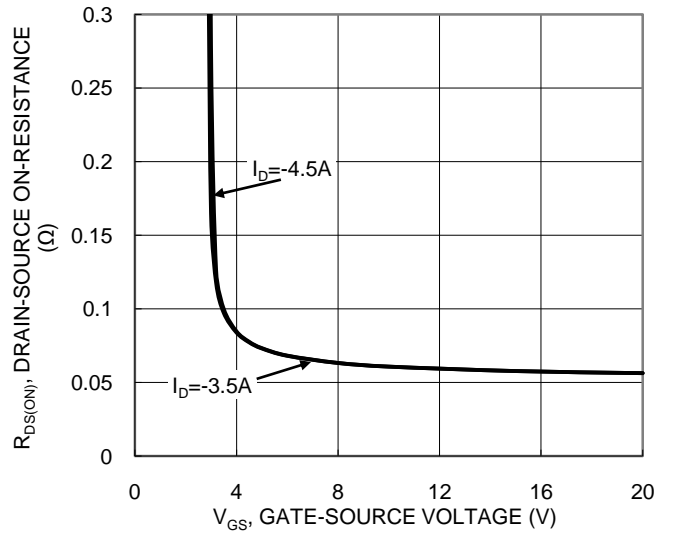


Figure 4. Typical Transfer Characteristic

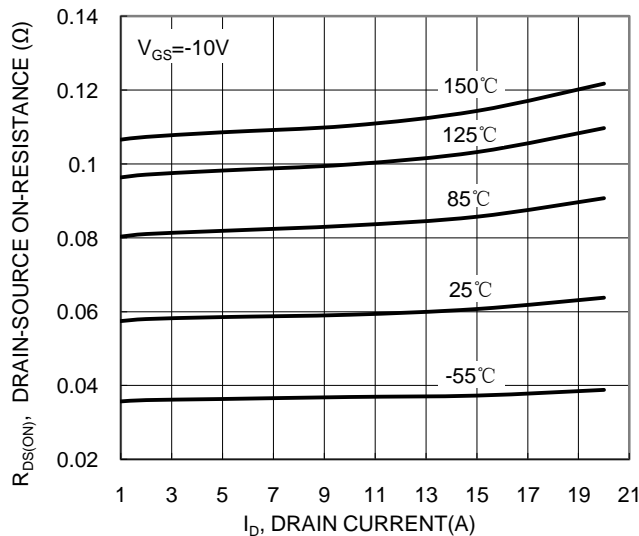


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

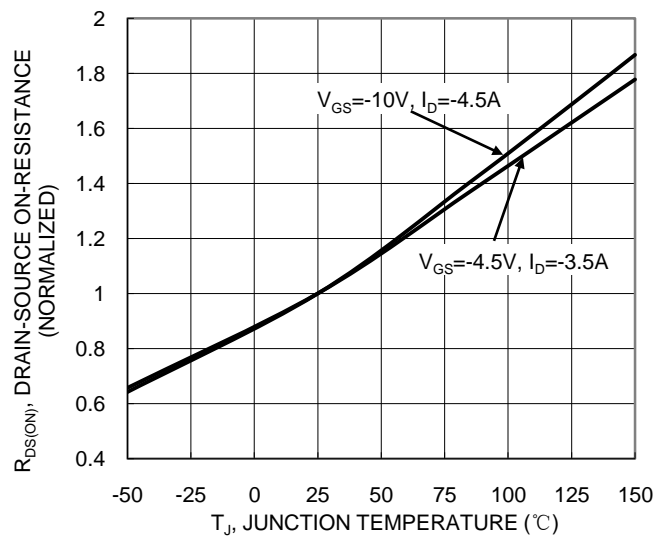


Figure 6. On-Resistance Variation with Temperature

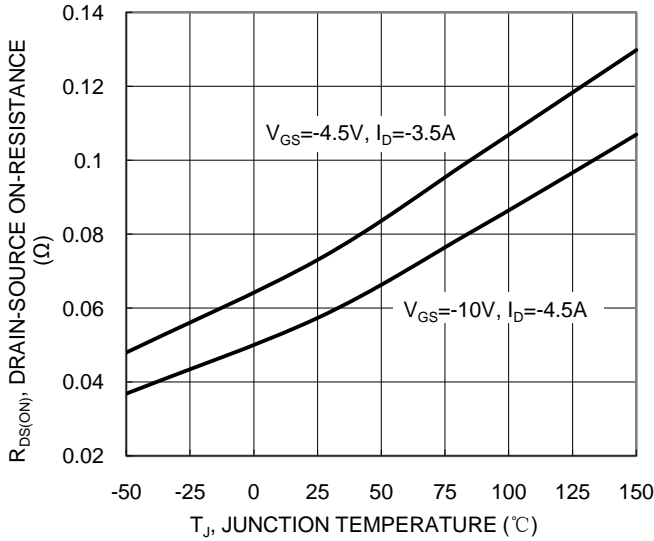


Figure 7. On-Resistance Variation with Temperature

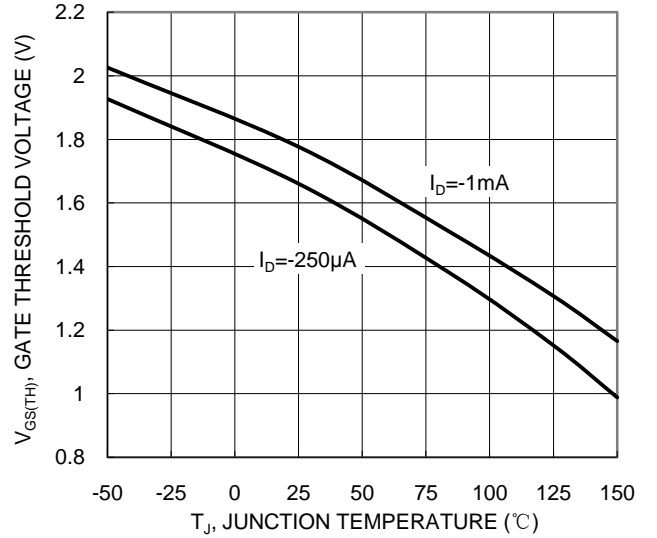


Figure 8. Gate Threshold Variation vs. Junction Temperature

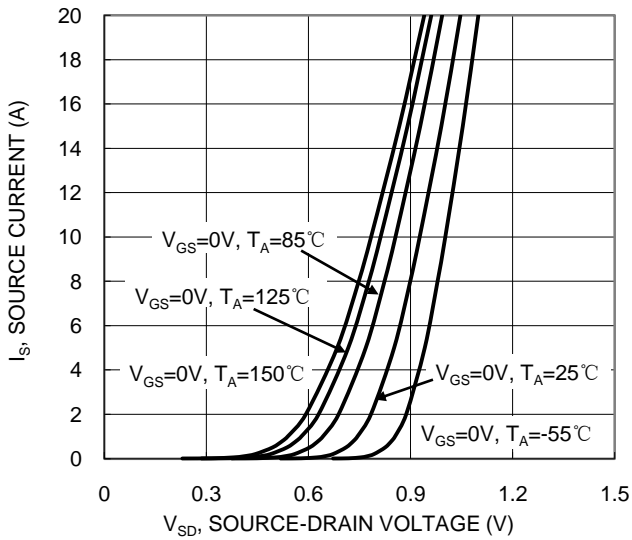


Figure 9. Diode Forward Voltage vs. Current

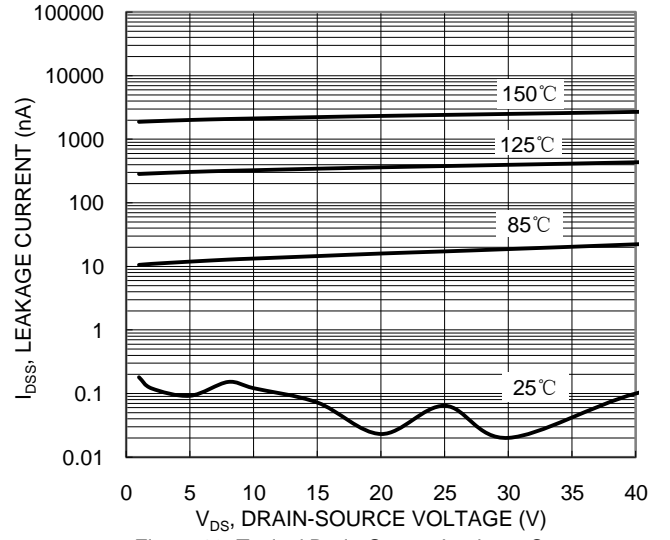


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

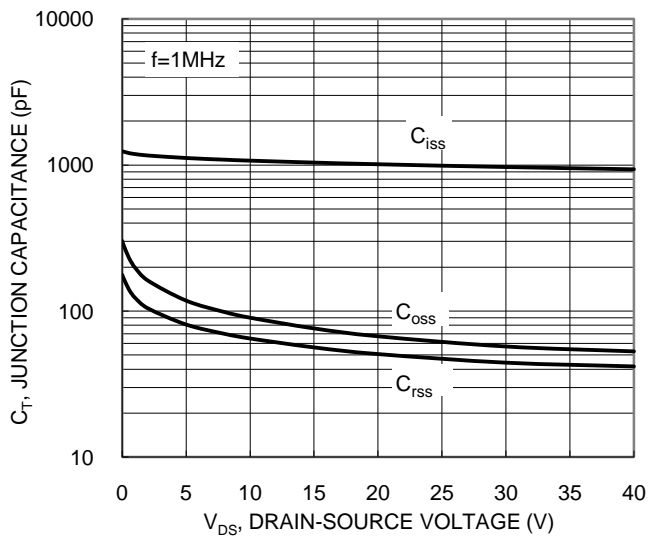


Figure 11. Typical Junction Capacitance

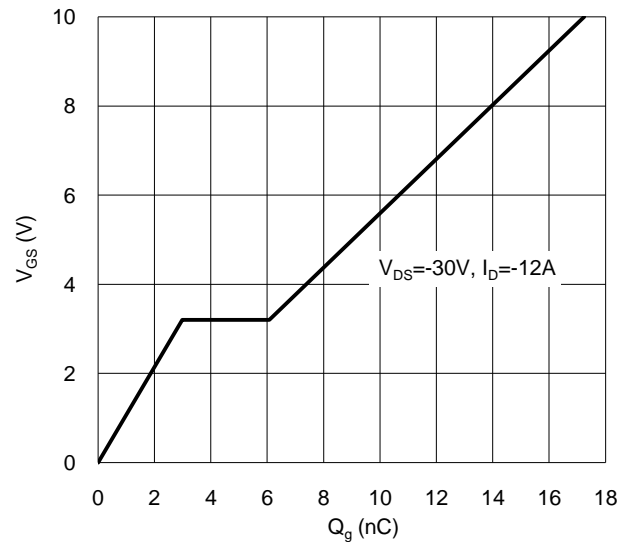


Figure 12. Gate Charge

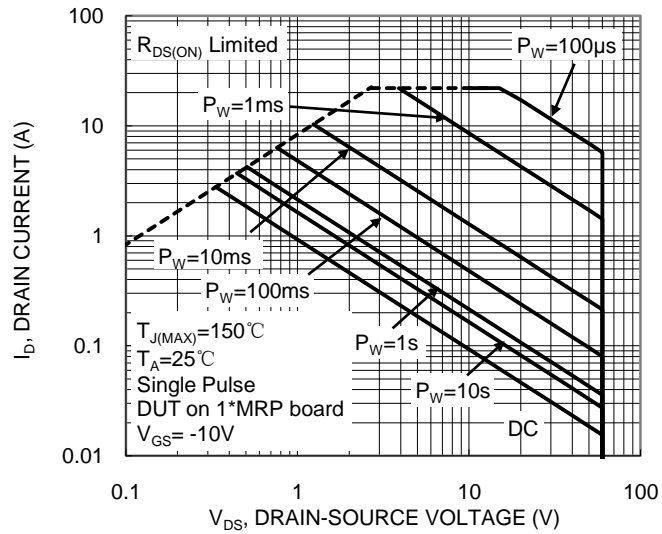


Figure 13. SOA, Safe Operation Area

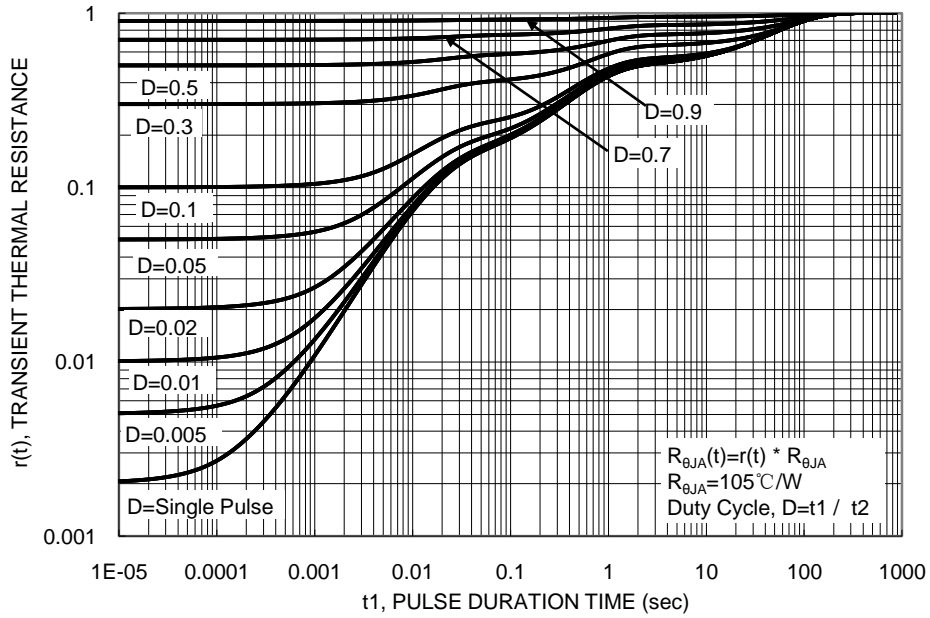
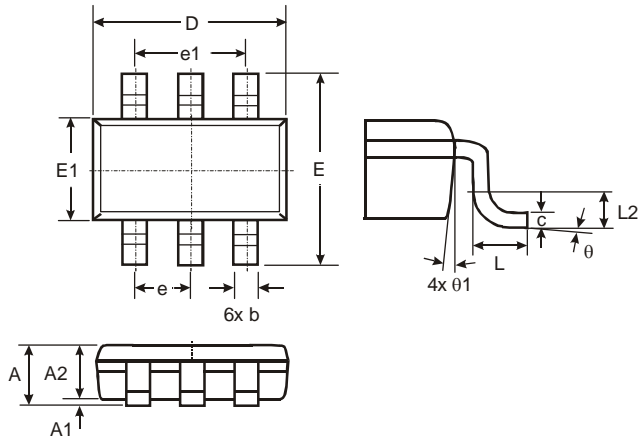


Figure 14. Transient Thermal Resistance

Package Outline Dimensions

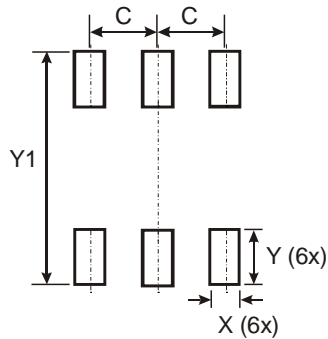
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TSOT26			
Dim	Min	Max	Typ
A	-	1.00	-
A1	0.01	0.10	-
A2	0.84	0.90	-
D	-	-	2.90
E	-	-	2.80
E1	-	-	1.60
b	0.30	0.45	-
c	0.12	0.20	-
e	-	-	0.95
e1	-	-	1.90
L	0.30	0.50	-
L2	-	-	0.25
θ	0°	8°	4°
θ1	4°	12°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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